

2SK1374

Silicon N-channel MOSFET

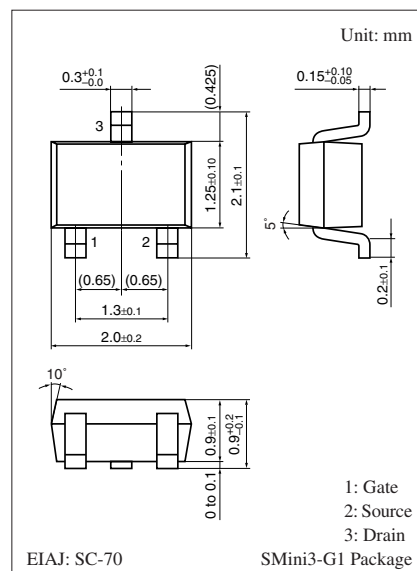
For switching circuits

■ Features

- High-speed switching
- Wide frequency band
- Incorporating a built-in gate protection-diode
- Allowing 2.5 V drive

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	50	V
Gate-source voltage (Drain open)	V_{GSO}	10	V
Drain current	I_D	50	mA
Peak drain current	I_{DP}	100	mA
Power dissipation	P_D	150	mW
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



Marking Symbol: 4V

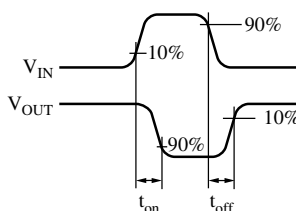
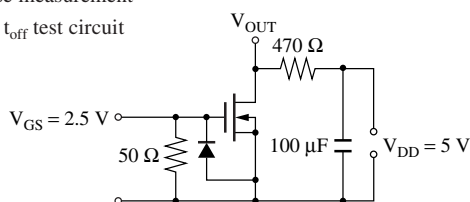
■ Electrical Characteristics $T_a = 25^\circ\text{C}$

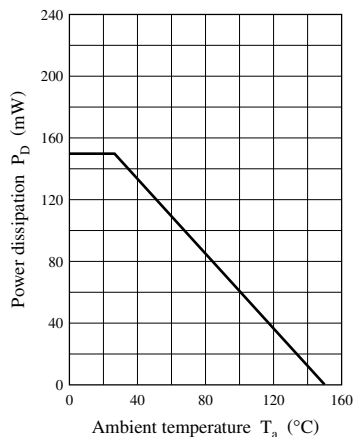
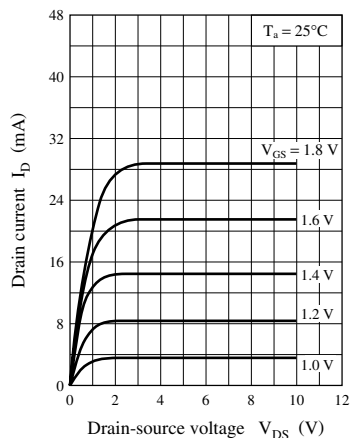
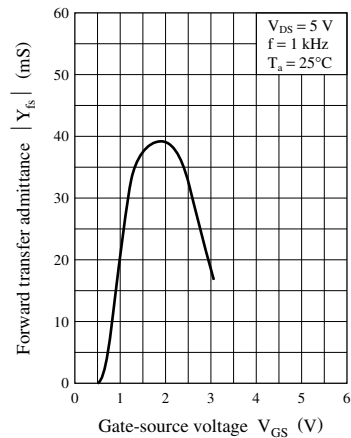
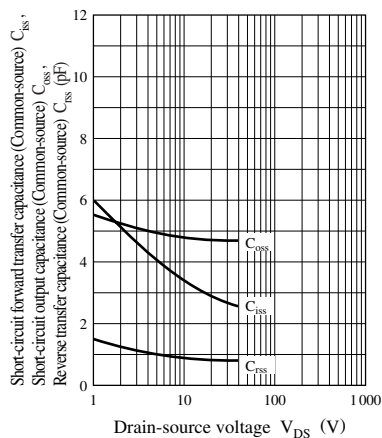
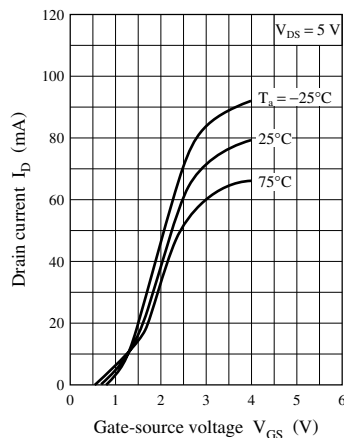
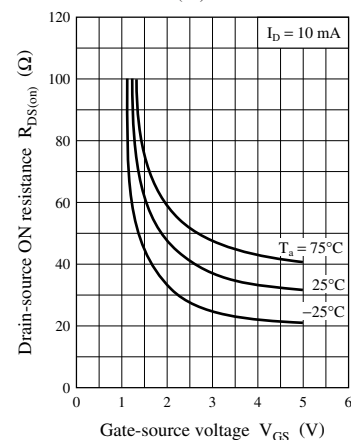
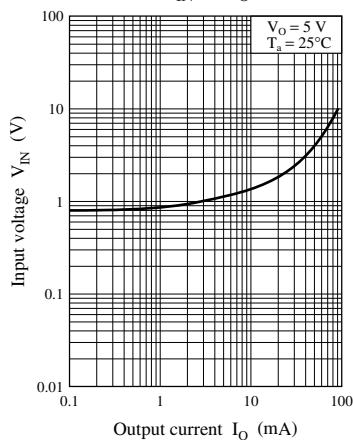
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	V_{DSS}	$I_D = 10\ \mu\text{A}$, $V_{GS} = 0$	50	100		V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 20\ \text{V}$, $V_{GS} = 0$			1.0	μA
Gate-source cutoff current	I_{GSS}	$V_{GS} = 10\ \text{V}$, $V_{DS} = 0$			1.0	μA
Gate threshold voltage	V_{th}	$I_D = 100\ \mu\text{A}$, $V_{DS} = 5\ \text{V}$	0.5	0.8	1.1	V
Forward transfer admittance	$ Y_{fs} $	$I_D = 10\ \text{mA}$, $V_{DS} = 5\ \text{V}$, $f = 1\ \text{kHz}$	20	39		mS
Drain-source ON resistance	$R_{DS(on)}$	$I_D = 10\ \text{mA}$, $V_{GS} = 2.5\ \text{V}$		27	50	Ω
Short-circuit forward transfer capacitance (Common source)	C_{iss}	$V_{DS} = 5\ \text{V}$, $V_{GS} = 0$, $f = 1\ \text{MHz}$		4.5		pF
Short-circuit output capacitance (Common source)	C_{oss}			4.1		pF
Reverse transfer capacitance (Common source)	C_{rss}			1.2		pF
Turn-on time *1, 2	t_{on}	$V_{DD} = 5\ \text{V}$, $R_L = 470\ \Omega$, $V_{GS} = 0\ \text{V}$ to $2.5\ \text{V}$		0.2		μs
Turn-off time *1, 2	t_{off}	$V_{DD} = 5\ \text{V}$, $R_L = 470\ \Omega$, $V_{GS} = 2.5\ \text{V}$ to $0\ \text{V}$		0.2		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

*2: t_{on} , t_{off} test circuit



$P_D - T_a$  $I_D - V_{DS}$  $|Y_{fs}| - V_{GS}$  $C_{iss}, C_{oss}, C_{rss} - V_{DS}$  $I_D - V_{GS}$  $R_{DS(on)} - V_{GS}$  $V_{IN} - I_O$ 

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